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# 2SC4995

Silicon NPN Epitaxial

# HITACHI

ADE-208-013  
1st. Edition

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## Application

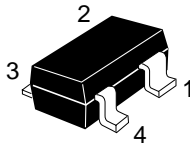
VHF / UHF wide band amplifier

## Features

- High gain bandwidth product  
 $f_T = 11 \text{ GHz Typ}$
- High gain, low noise figure  
 $PG = 16.5 \text{ dB Typ}$ ,  $NF = 1.1 \text{ dB Typ}$  at  $f = 900 \text{ MHz}$

## Outline

CMPAK-4



1. Collector
2. Emitter
3. Base
4. Emitter

**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	15	V
Collector to emitter voltage	$V_{\text{CEO}}$	8	V
Emitter to base voltage	$V_{\text{EBO}}$	1.5	V
Collector current	$I_{\text{C}}$	50	mA
Collector power dissipation	$P_{\text{C}}$	100	mW
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

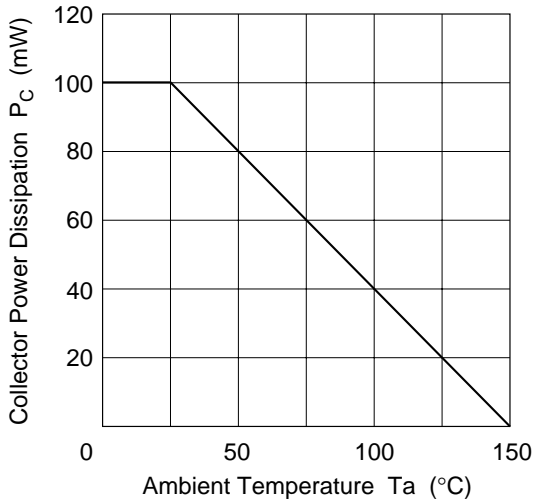
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	15	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$ , $I_{\text{E}} = 0$
Collector cutoff current	$I_{\text{CBO}}$	—	—	10	$\mu\text{A}$	$V_{\text{CB}} = 12 \text{ V}$ , $I_{\text{E}} = 0$
	$I_{\text{CEO}}$	—	—	1	mA	$V_{\text{CE}} = 8 \text{ V}$ , $R_{\text{BE}} = \infty$
Emitter cutoff current	$I_{\text{EBO}}$	—	—	10	$\mu\text{A}$	$V_{\text{EB}} = 1.5 \text{ V}$ , $I_{\text{C}} = 0$
DC current transfer ratio	$h_{\text{FE}}$	50	120	250		$V_{\text{CE}} = 5 \text{ V}$ , $I_{\text{C}} = 20 \text{ mA}$
Collector output capacitance	$C_{\text{ob}}$	—	0.55	1.05	pF	$V_{\text{CB}} = 5 \text{ V}$ , $I_{\text{E}} = 0$ , $f = 1 \text{ MHz}$
Gain bandwidth product	$f_{\text{T}}$	8.0	11.0	—	GHz	$V_{\text{CE}} = 5 \text{ V}$ , $I_{\text{C}} = 20 \text{ mA}$
S21 Parameter	$ S_{21} $	—	16	—	dB	$V_{\text{CE}} = 5 \text{ V}$ , $I_{\text{C}} = 20 \text{ mA}$ , $f = 1000 \text{ MHz}$
Power gain	PG	13.5	16.5	—	dB	$V_{\text{CE}} = 5 \text{ V}$ , $I_{\text{C}} = 20 \text{ mA}$ , $f = 900 \text{ MHz}$
Noise figure	NF	—	1.1	2.0	dB	$V_{\text{CE}} = 5 \text{ V}$ , $I_{\text{C}} = 5 \text{ mA}$ , $f = 900 \text{ MHz}$

Note: Marking is “YD-”.

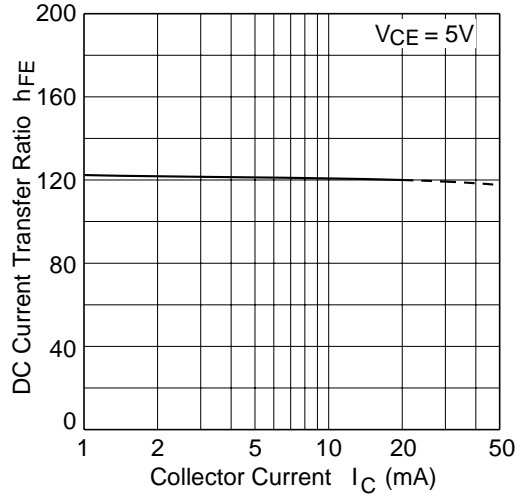
Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

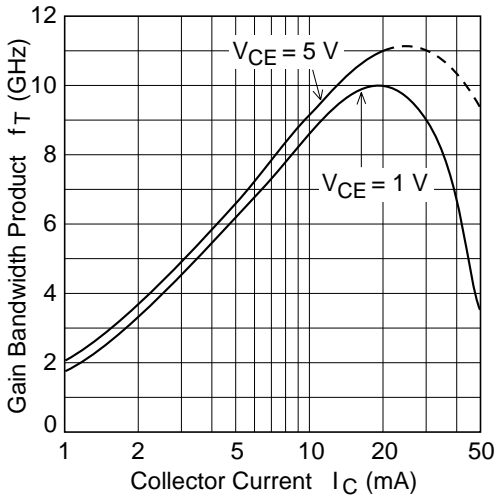
Maximum Collector Dissipation Curve



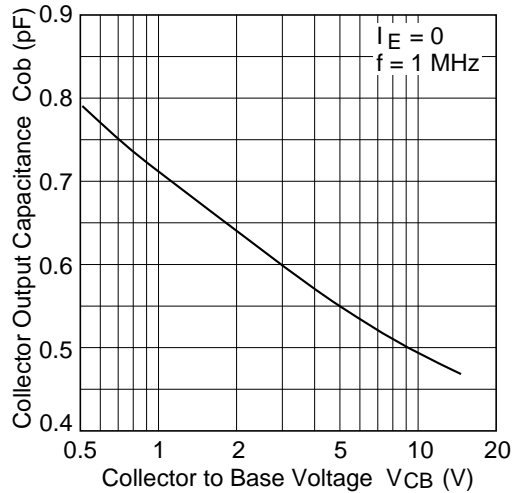
DC Current Transfer Ratio vs. Collector Current



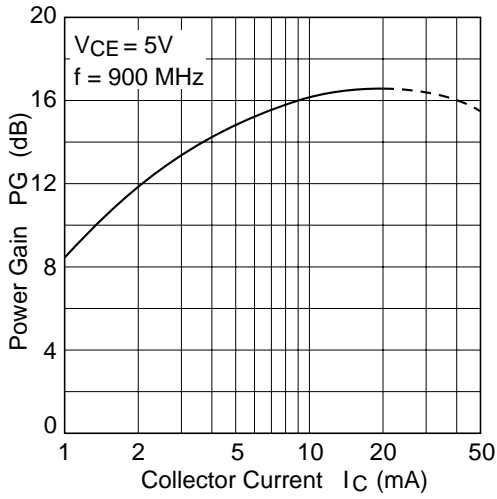
Gain Bandwidth Product vs. Collector Current



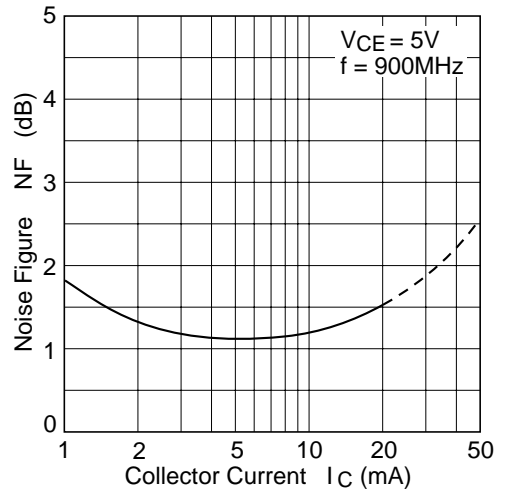
Collector Output Capacitance vs. Collector to Base Voltage



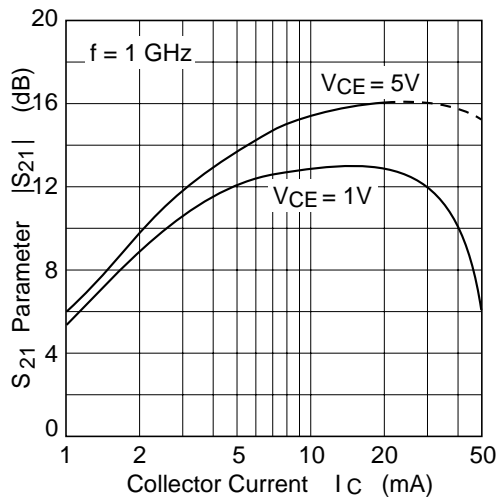
Power Gain vs. Collector Current



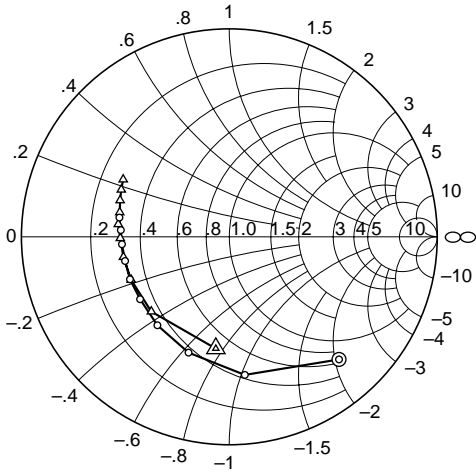
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current

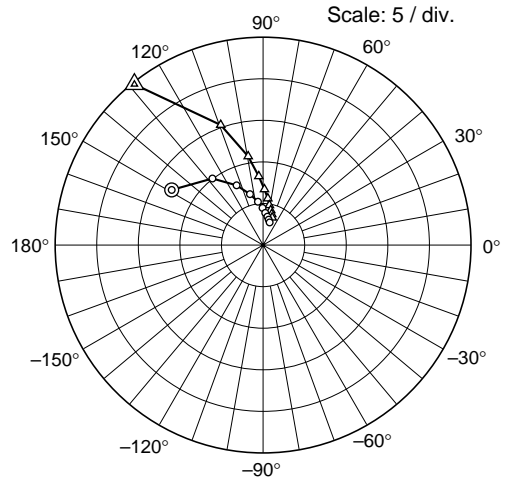


S11 Parameter vs. Frequency



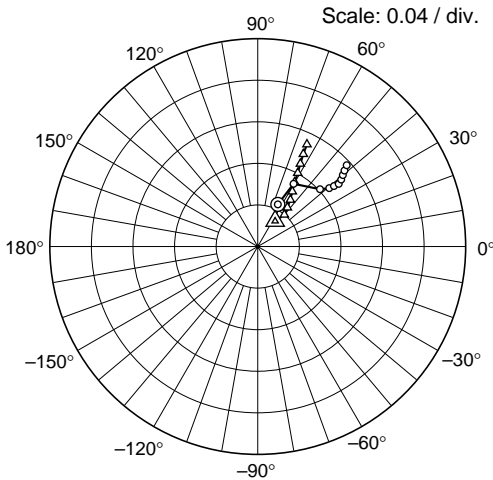
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S21 Parameter vs. Frequency



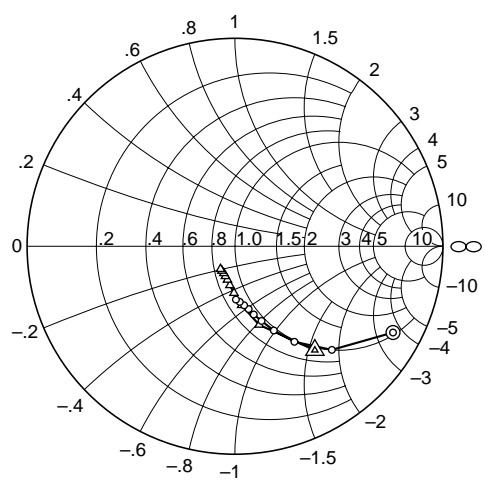
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S12 Parameter vs. Frequency



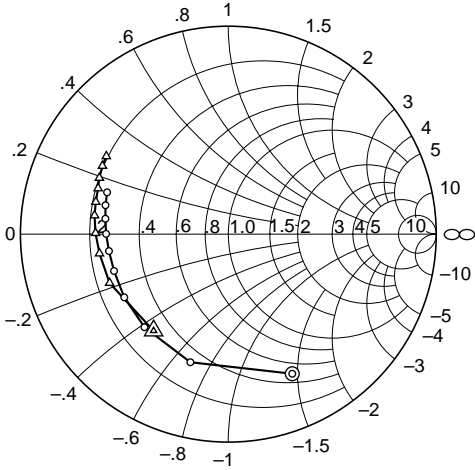
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S22 Parameter vs. Frequency



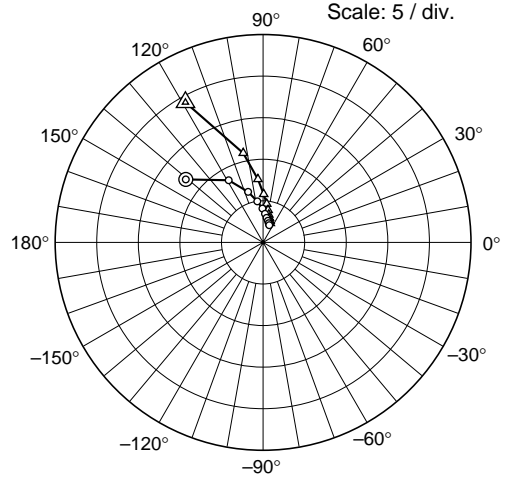
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S11 Parameter vs. Frequency



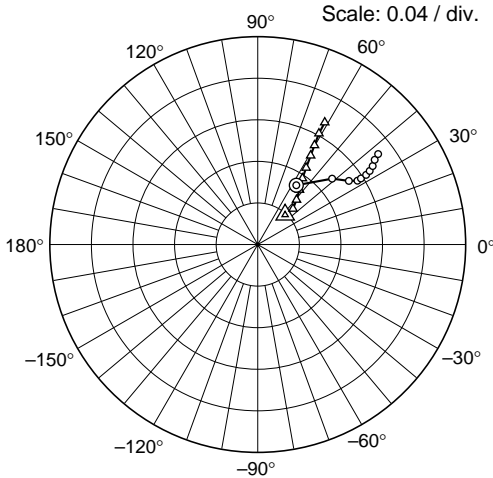
Condition:  $V_{CE} = 1\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S21 Parameter vs. Frequency



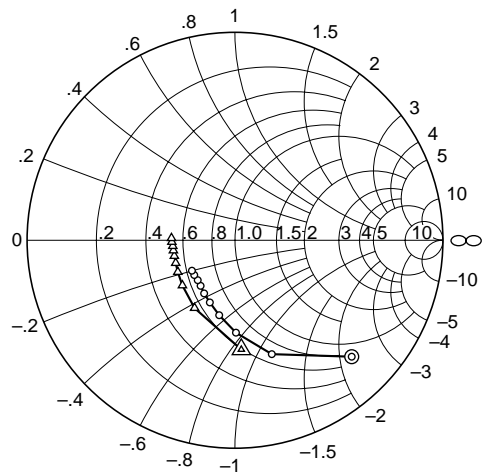
Condition:  $V_{CE} = 1\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S12 Parameter vs. Frequency



Condition:  $V_{CE} = 1\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

S22 Parameter vs. Frequency



Condition:  $V_{CE} = 1\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ — ○ ( $I_C = 5\text{ mA}$ )  
 △ — △ ( $I_C = 20\text{ mA}$ )

**S Parameter** ( $V_{CE} = 5\text{ V}$ ,  $I_C = 5\text{ mA}$ ,  $Z_O = 50\ \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.781	-48.2	12.84	148.8	0.0449	64.6	0.866	-28.6
400	0.669	-83.6	10.04	127.3	0.0695	50.3	0.682	-46.9
600	0.591	-109.4	7.84	113.9	0.0815	42.6	0.541	-58.1
800	0.549	-129.1	6.30	104.4	0.0889	39.2	0.446	-65.2
1000	0.524	-145.0	5.23	96.7	0.0937	38.4	0.381	-70.4
1200	0.520	-156.8	4.45	90.7	0.0986	37.7	0.340	-74.6
1400	0.515	-166.9	3.86	86.0	0.103	38.7	0.309	-77.7
1600	0.518	-176.0	3.44	81.1	0.107	40.0	0.287	-81.2
1800	0.523	176.5	3.11	77.3	0.111	41.2	0.268	-85.1
2000	0.537	170.1	2.82	73.5	0.116	42.4	0.256	-89.0

**S Parameter** ( $V_{CE} = 5\text{ V}$ ,  $I_C = 20\text{ mA}$ ,  $Z_O = 50\ \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.542	-69.9	24.74	128.7	0.0296	55.5	0.631	-52.5
400	0.520	-136.2	15.31	109.4	0.0398	50.2	0.395	-72.9
600	0.516	-156.3	10.81	99.5	0.0470	52.8	0.285	-83.6
800	0.519	-169.1	8.29	93.5	0.0547	55.1	0.225	-91.3
1000	0.525	-179.2	6.70	88.5	0.0624	57.9	0.189	-97.5
1200	0.538	173.6	5.63	84.1	0.0712	60.2	0.166	-102.8
1400	0.540	167.5	4.85	80.9	0.0805	61.5	0.151	-107.9
1600	0.554	161.6	4.29	77.5	0.0895	62.8	0.140	-112.6
1800	0.567	159.5	3.86	74.3	0.0991	63.8	0.134	-118.1
2000	0.580	151.7	3.48	71.6	0.109	64.3	0.129	-122.5

## 2SC4995

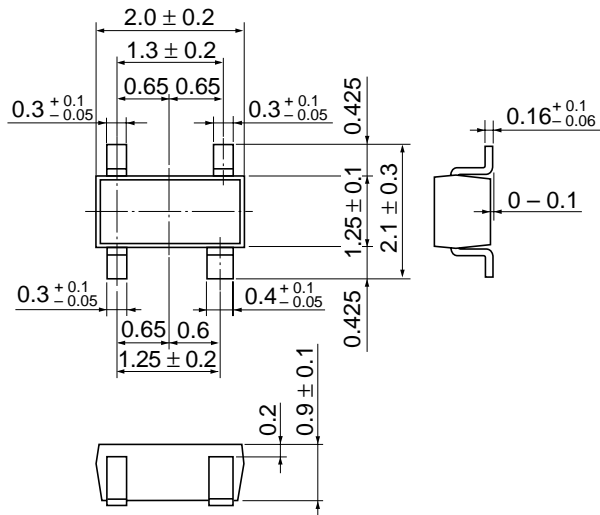
### S Parameter ( $V_{CE} = 1 \text{ V}$ , $I_C = 5 \text{ mA}$ , $Z_O = 50 \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.739	-65.4	11.99	140.8	0.0681	56.9	0.793	-44.9
400	0.643	-106.5	8.54	118.9	0.0957	41.5	0.576	-72.1
600	0.603	-132.0	6.34	106.4	0.107	34.9	0.446	-89.4
800	0.586	-148.7	4.99	97.9	0.114	32.6	0.369	-101.9
1000	0.578	-162.1	4.08	90.9	0.118	32.6	0.323	-112.0
1200	0.580	-171.9	3.45	86.0	0.124	32.7	0.396	-120.1
1400	0.588	179.9	2.99	81.7	0.129	33.3	0.275	-127.0
1600	0.596	172.9	2.67	77.2	0.134	34.3	0.263	-133.0
1800	0.607	166.8	2.41	73.4	0.139	35.9	0.256	-139.5
2000	0.617	161.0	2.20	70.0	0.145	36.9	0.254	-144.7

### S Parameter ( $V_{CE} = 1 \text{ V}$ , $I_C = 20 \text{ mA}$ , $Z_O = 50 \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.588	-127.7	19.25	119.0	0.0389	47.2	0.527	-86.7
400	0.618	-157.6	11.00	102.5	0.0483	45.3	0.380	-120.8
600	0.627	-171.4	7.62	94.6	0.0570	49.0	0.334	-139.3
800	0.639	179.6	5.80	89.2	0.0662	52.6	0.315	-150.9
1000	0.650	172.1	4.66	84.5	0.0768	55.9	0.306	-158.9
1200	0.656	-166.4	3.94	81.1	0.873	57.7	0.302	-165.4
1400	0.664	160.7	3.40	78.2	0.0996	59.2	0.301	-170.5
1600	0.677	156.5	3.03	75.2	0.110	60.2	0.301	-174.6
1800	0.689	151.6	2.71	71.9	0.122	61.1	0.304	-178.4
2000	0.696	147.5	2.47	69.2	0.134	61.2	0.306	178.2





Hitachi Code	CMPAK-4(T)
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.006 g

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